



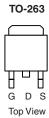
N-Channel 60-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{(BR)DSS} (V)	$r_{DS(on)}\left(\Omega\right)$	I _D (A)			
60	0.0034 at V _{GS} = 10 V	110 ^a			
	0.0041 at V _{GS} = 4.5 V	110			

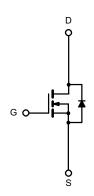
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g Tested





Ordering Information: SUM110N06-3m4L-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A =$	25 °C, unless other	wise noted			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _{.I} = 175 °C)	T _C = 25 °C	L	110 ^a		
Continuous Diam Guitent (1) = 173 C)	T _C = 125 °C	l _D	110 ^a		
Pulsed Drain Current		I _{DM}	440	7 ^	
Avalanche Current, Single Pulse		I _{AS}	75	1	
Avalanche Energy, Single Pulse	L = 0.1 mH	E _{AS}	280	mJ	
Manianus Davis Discipation	T _C = 25 °C	В	375 ^b	14/	
Maximum Power Dissipation	T _A = 25 °C ^c	P _D –	3.75	W	
Operating Junction and Storage Temperature Range	•	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Unit	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4		

Notes:

- a. Package limited.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).

SUM110N06-3m4L

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static				1 -71-			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1		3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50		
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			10	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α	
Drain-Source On-State Resistance ^a	``,	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$		0.0028	0.0034		
		V _{GS} = 4.5 V, I _D = 20 A		0.0033	0.0041		
	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C			0.0055	Ω	
		V _{GS} = 10 V, I _D = 30 A, T _J = 175 °C			0.007		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 30 \text{ A}$	30			S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		12900		pF	
Output Capacitance	C _{oss}			1060			
Reverse Transfer Capacitance	C _{rss}			700			
Total Gate Charge ^c	Qg			200	300	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 110 \text{ A}$		50			
Gate-Drain Charge ^c	Q_{gd}			33			
Gate Resistance	Rg	f = 1.0 MHz	0.65	1.3	2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			22	35		
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.4 Ω $I_D \cong 110$ A, V_{GEN} = 10 V, R_g = 2.5 Ω		130	200	ns	
Turn-Off Delay Time ^c	t _{d(off)}			110	165		
Fall Time ^c	t _f			280	420		
Source-Drain Diode Ratings and Cha	aracteristics 7	「 _C = 25 °C ^b					
Continuous Current	I _S				110		
Pulsed Current	I _{SM}				440	A	
Forward Voltage ^a	V _{SD}	I _F = 110 A, V _{GS} = 0 V		1.0	1.5	V	
Reverse Recovery Time	t _{rr}			55	82	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	I _E = 110 A, di/dt = 100 A/μs		3.6	5.4	Α	
Reverse Recovery Charge	Q _{rr}	' '		0.1	0.22	uС	

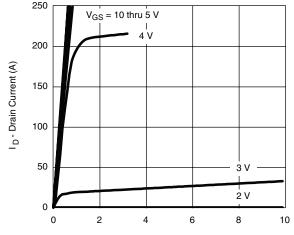
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

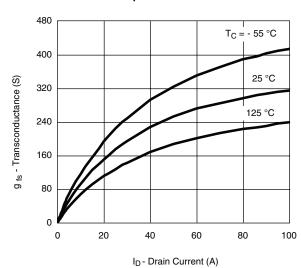


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

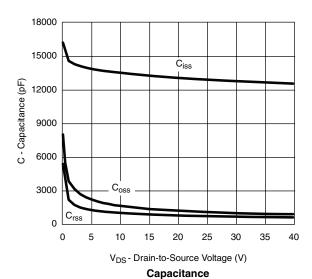


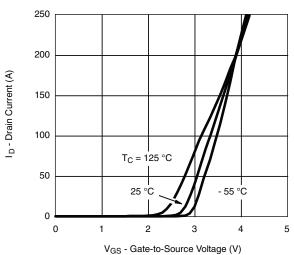
V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics

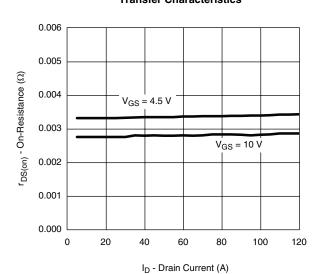


Transconductance

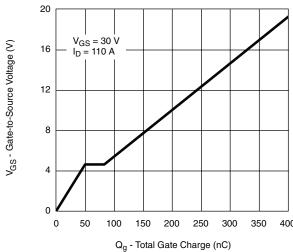




Transfer Characteristics



On-Resistance vs. Drain Current



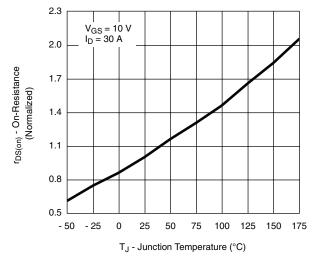
Cata Charge

Gate Charge

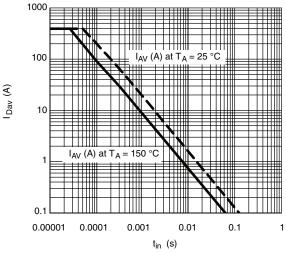
Vishay Siliconix

VISHAY.

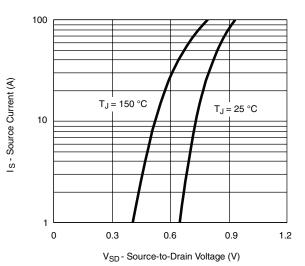
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



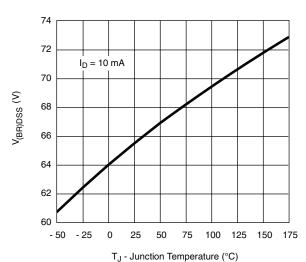
On-Resistance vs. Junction Temperature



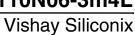
Avalanche Current vs. Time



Source-Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature





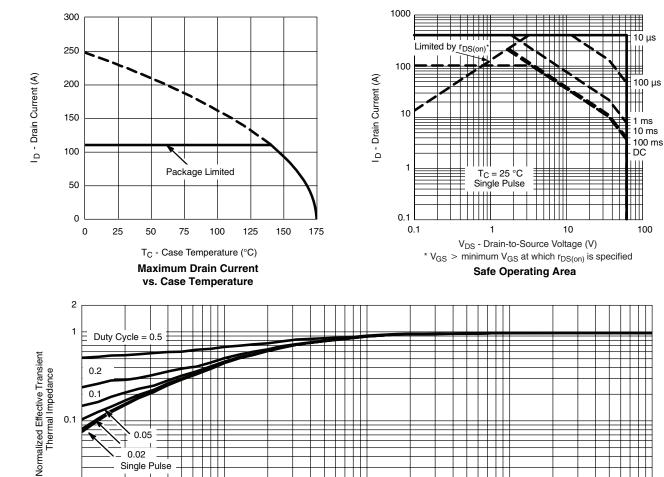
THERMAL RATINGS

0.02 Single Pulse

10⁻³

0.01

10⁻⁴



Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Case

10⁻¹

5

10⁻²

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73036.



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.